基本半导体
BASiC Semiconductor

B2DM100120N1

SiC Schottky Diode

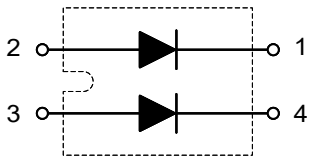
Product Summary

V_{RRM}	1200 V
I_F (T_C=120°C)	100 A*
Q_C	465 nC*

Package: SOT-227

*Backside is isolated

Electrical Connection



Features

- Low leakage current (I_R)
- Zero reverse recovery current
- Temperature independent switching behavior
- Positive temperature coefficient on V_F
- High surge current capacity
- Low capacitive charge

Halogen

RoHS

Benefits

- Copper base plate with AlN isolation for low thermal resistance
- System cost savings due to smaller magnetics
- System efficiency improvement over Si diodes
- Reduction of heat sink requirements
- Enabling higher frequency
- Reduced EMI
- Isolation voltage: 2500V

Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- Server/telecom power supplies
- Power factor correction
- Solar

Package Pin Definitions

- Pin 1,4 - Cathode
- Pin 2,3 - Anode

Package Parameters

Part Number	Marking	Package
B2DM100120N1	B2DM100120N1	SOT-227

* Per Leg, ** Per Device

Maximum Ratings (T_c=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1200	V
V_{RSM}	Non-repetitive peak reverse voltage		1200	V
I_F	Continuous forward current	T_C=25°C	175*/350**	A
		T_C=120°C	100*/200**	
I_{FSM}	Non-repetitive forward surge current	T_C=25°C, t_p=10ms Half sine wave	540*	A
$\int i^2dt$	i²t value	T_C=25°C, t_p=10ms	1450*	A^2S
P_{tot}	Power dissipation	T_C=25°C T_C=110°C	652*/1304** 283*/566**	W
T_j	Operating junction temperature		-55~175	°C
T_{stg}	Storage temperature		-55~175	°C

* Per Leg, ** Per Device

Thermal and Mechanical Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case			0.24*/ 0.12**		K/W
M_d	Mounting torque	M4-0.7 screws			1.5	N/m
M_{dt}	Terminal connection torque	M4-0.7 screws			1.3	N/m
W_t	Package weight			29		g
V_{ISOL}	Isolation voltage	I_{ISOL}<1mA, RMS, 50Hz,1min	2500			V
d_{Ctt}	Creepage Distance on Surface	Terminal to Terminal	10.4			mm
d_{Ctb}		Terminal to Backside	9.6			mm
d_{Stt}	Clearance Distance Through Air	Terminal to Terminal	4.4			mm
d_{Stb}		Terminal to Backside	8.4			mm
	Internal isolation		AlN			

* Per Leg, ** Per Device

Electrical Characteristics(Per Leg)
Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{DC}	DC blocking voltage	T_j=25°C	1200			V
V_F	Diode forward voltage	I_F=100A T_j=25°C I_F=100A T_j=175°C		1.53 2.3	1.9 3.1	V
I_R	Reverse current	V_R=1200V T_j=25°C V_R=1200V T_j=175°C		10 90	700 900	μA

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q_C	Total capacitive charge	V_R=800V T_j=25°C $Q_C=\int_0^{V_R} C(V)dV$		465		nC
C	Total capacitance	V_R=1V f=1MHz V_R=400V f=1MHz V_R=800V f=1MHz		5843 430 330		pF
E_C	Capacitance stored energy	V_R=800V		240		μJ

Typical Performance(Per Leg)

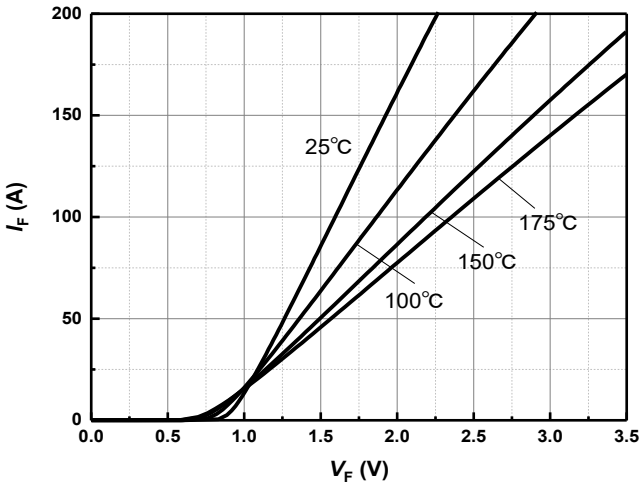


Figure 1 **Typical forward characteristics**

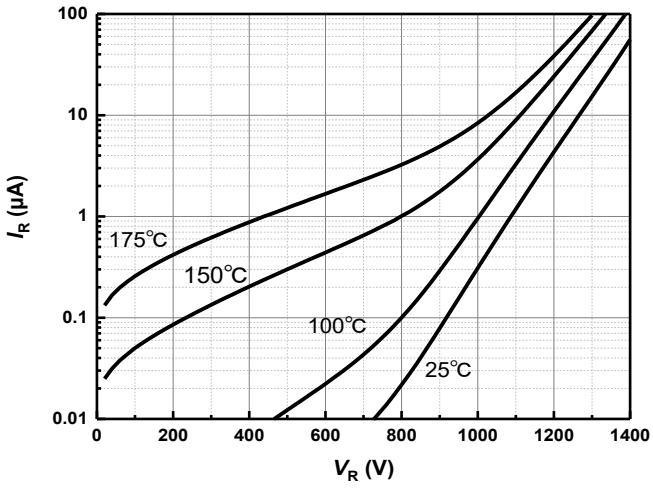


Figure 2 **Typical reverse current as function of reverse voltage**

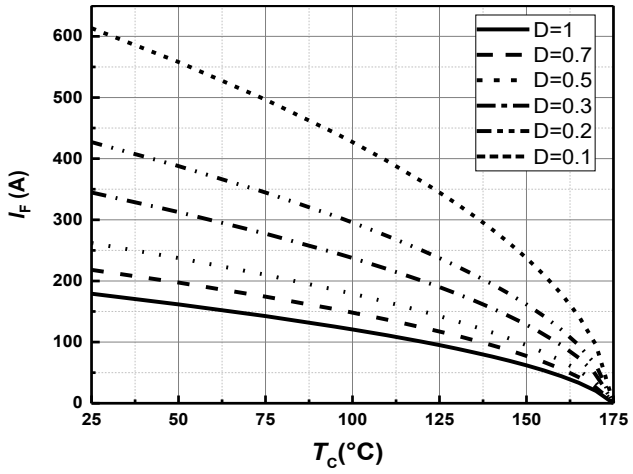


Figure 3 **Diode forward current as function of temperature, D=duty cycle**

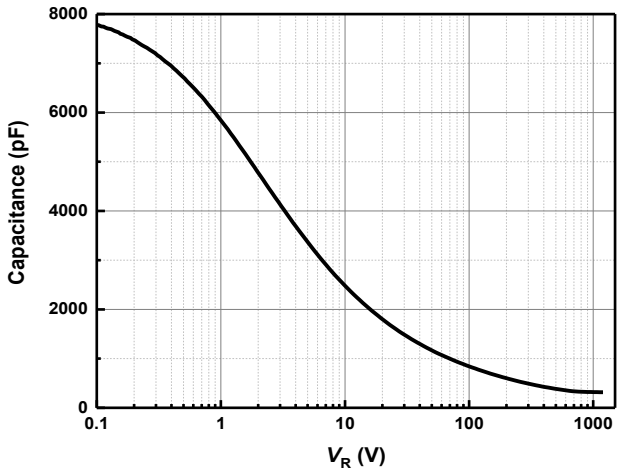


Figure 4 **Typical capacitance as function of reverse voltage, C=f(V_R); T_j=25°C; f=1 MHz**

Typical Performance

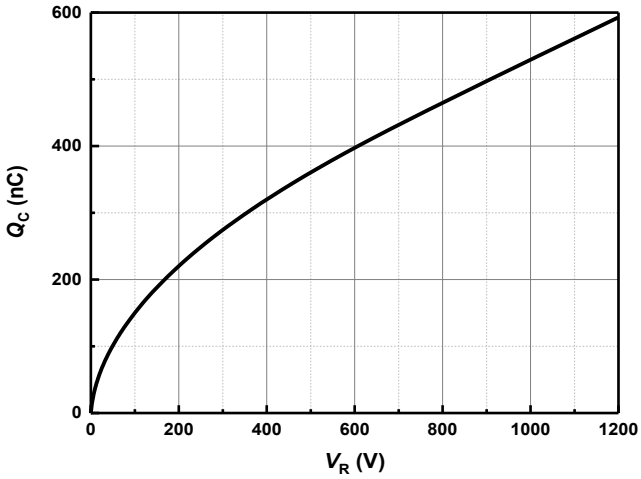


Figure 5 Typical reverse charge as function of reverse voltage

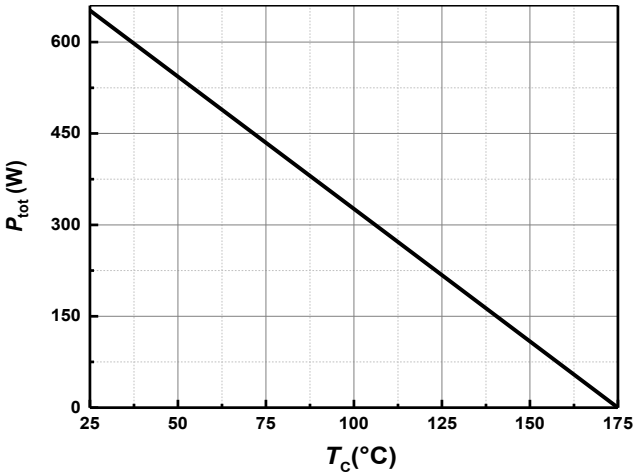


Figure 6 Power dissipation as function of case temperature

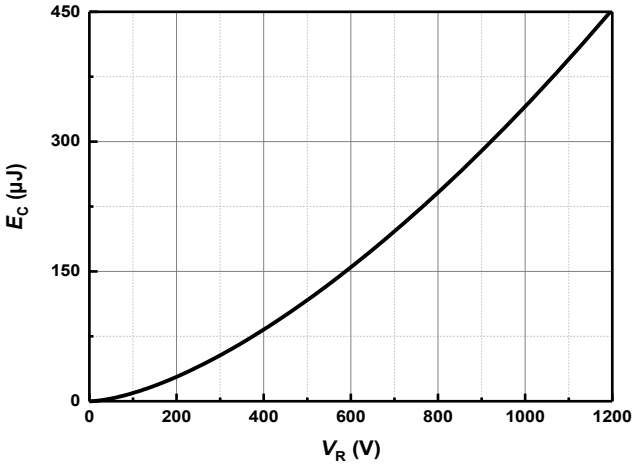


Figure 7 Capacitance stored energy

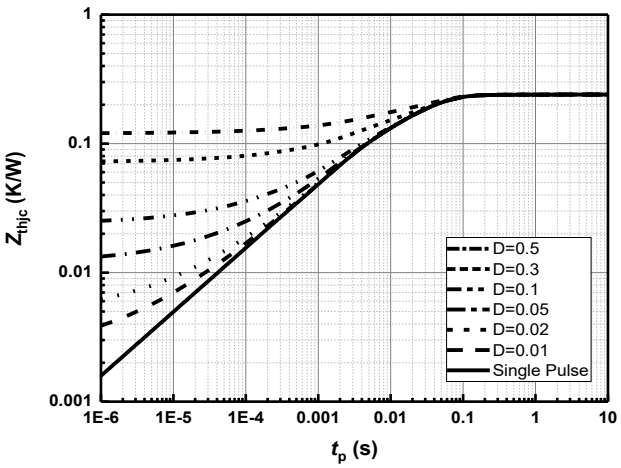
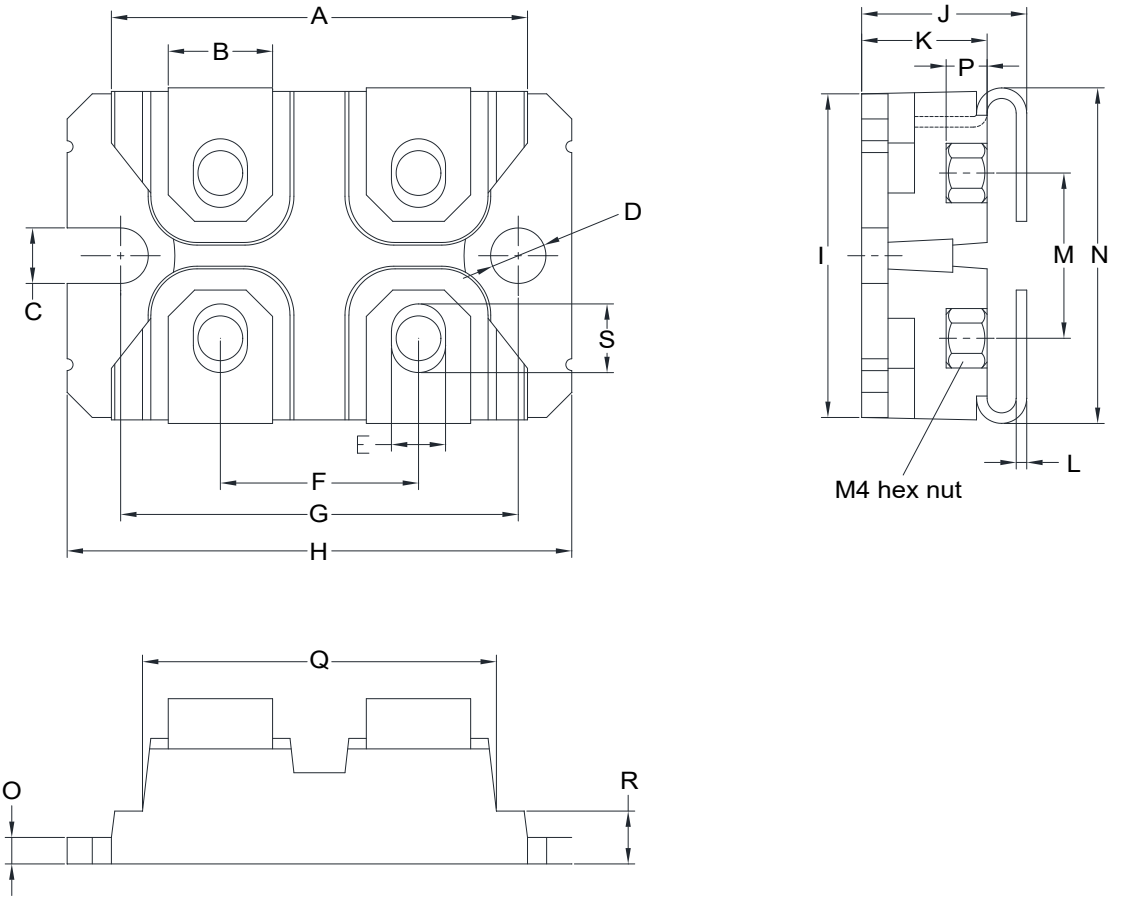


Figure 8 Max. transient thermal impedance, Z_{thjc}= f(t), parameter: $D = t / T$

Package Dimensions



Items	mm	
	MIN	MAX
A	31.40	31.60
B	7.70	8.10
C	4.20	4.40
D	4.20	4.40
E	4.10	4.30
F	14.90	15.10
G	30.10	30.20
H	38.00	38.40
I	23.80	24.20
J	12.20	12.70
K	9.40	9.60
L	0.75	0.85
M	12.40	12.60
N	24.50	25.40
O	1.90	2.10
P	3.10	3.20
Q	26.60	27.00
R	3.80	4.20
S	5.10	5.40

Revision History

Document Version	Date of Release	Description of Changes
Rev. 0.0	2022-11-15	Release of the datasheet.
Rev. 0.1	2023-07-04	Characteristics update.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest BASiC Semiconductor Office

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